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(54) **SEMICONDUCTOR DEVICE AND MANUFACTURING METHOD FOR SEMICONDUCTOR DEVICE**

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(57) **ABSTRACT**

There is provided a semiconductor equipment including: an element area having an n-type layer, a first p-type layer on the n-type layer, and a second p-type layer on the first p-type layer, the second p-type layer having an acceptor concentration higher than the first p-type layer; and an electric field relaxation region surrounding the element area, in which in the electric field relaxation region, a region containing an impurity element that inactivates a part of acceptors in the first p-type layer and the second p-type layer is provided in the first p-type layer and the second p-type layer.